

Product data sheet

1. General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- Fast switching
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage			-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 121 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		-	-	15	A
Static character	Static characteristics						
V _F	forward voltage	I _F = 15 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.4	2	V
Dynamic characteristics							
t _{rr}	reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 200 A/µs; T _j = 25 °C; <u>Fig. 7</u>		-	13	18	ns





5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	к	cathode	mb	K – K – A
2	А	anode	$2 \circ 4$	001aaa020
mb	mb	mounting base; connected to cathode	C C C C C C C C C C C C C C	

6. Ordering information

Table 3. Ordering in	formation					
Type number	Package					
	Name	Description	Version			
BYC15-600P	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BYC15-600P	BYC15-600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

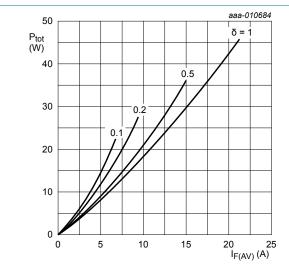
repetitive peak reverse voltage crest working reverse voltage		-	600	V
crest working reverse voltage				-
e e		-	600	V
everse voltage	DC	-	600	V
average forward current	δ = 0.5; T _{mb} ≤ 121 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	15	A
epetitive peak forward current	δ = 0.5; t _p = 25 µs; T _{mb} ≤ 121 °C; square-wave pulse	-	30	A
3	verage forward current epetitive peak forward current	verage forward current $\delta = 0.5$; $T_{mb} \le 121$ °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3epetitive peak forward current $\delta = 0.5$; $t_p = 25 \ \mu\text{s}$; $T_{mb} \le 121$ °C;	Inverse $\delta = 0.5; T_{mb} \le 121 \ ^{\circ}C; \text{ square-wave pulse}; Fig. 1; Fig. 2; Fig. 3-Inverse\delta = 0.5; T_p = 25 \ \mu\text{s}; T_{mb} \le 121 \ ^{\circ}C; \text{ square-wave pulse}-$	average forward current $\delta = 0.5; T_{mb} \le 121 \ ^{\circ}C; \text{ square-wave}$ pulse; Fig. 1; Fig. 2; Fig. 3-15epetitive peak forward current $\delta = 0.5; t_p = 25 \ \mu\text{s}; T_{mb} \le 121 \ ^{\circ}C;$ square-wave pulse-30

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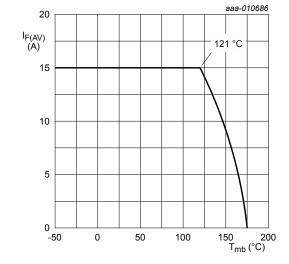
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Symbol	Parameter	Conditions	Min	Max	Unit
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; <u>Fig. 4</u>	-	180	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	200	A
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C





$I_{F(AV)} = I_{F(RMS)} imes \sqrt{oldsymbol{\delta}}$	
$V_{\rm O} = 1.578 \mathrm{V}; \mathrm{R}_{\mathrm{S}} = 0.027 \Omega$	





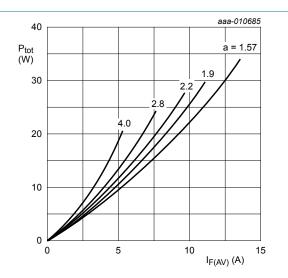
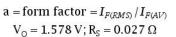
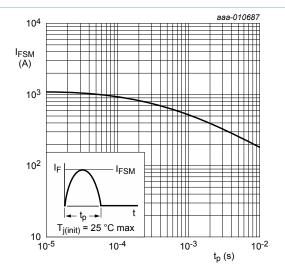


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values



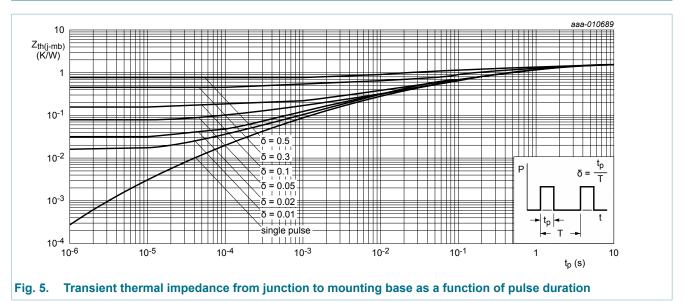


4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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9. Thermal characteristics

Table 6. T	hermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	1.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



10. Characteristics

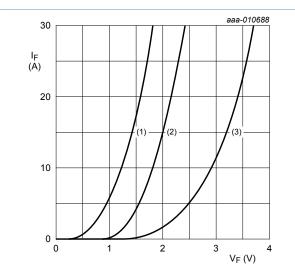
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics	· · · · ·	l l			
V _F forward voltage	I _F = 15 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.7	3.2	V	
		I _F = 15 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.4	2	V
I _R reve	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	1	mA
Dynamic cl	naracteristics		I			
Q _r recovered char	recovered charge	$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 \text{ °C}; Fig. 7$	-	30	-	nC
		I_F = 15 A; V_R = 200 V; dI_F/dt = 200 A/ µs; T_i = 125 °C; Fig. 7	-	115	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{d} I_F/\text{d} t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	13	18	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/$ µs; $T_j = 25 \text{ °C}; Fig. 7$	-	22	-	ns
		I _F = 15 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 25 °C; <u>Fig. 7</u>	-	28	-	ns
		I _F = 15 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 125 °C; <u>Fig. 7</u>	-	39	-	ns
I _{RM}	peak reverse recovery current	I _F = 15 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 25 °C; <u>Fig. 7</u>	-	2.1	-	A
		I _F = 15 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 125 °C; <u>Fig. 7</u>	-	5.8	-	A





(1) $T_j = 150$ °C; typical values; (2) $T_j = 150$ °C; maximum values; (3) $T_j = 25$ °C; maximum values; $V_0 = 1.578$ V; $R_s = 0.027 \Omega$

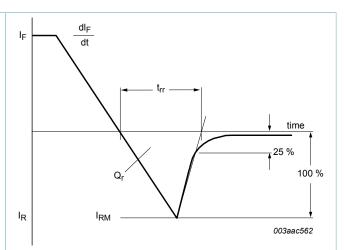
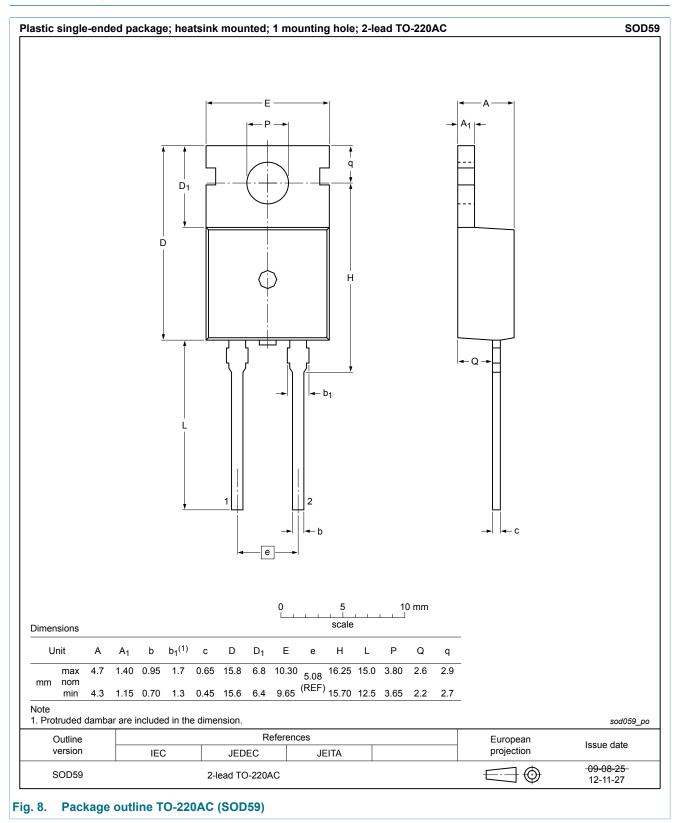


Fig. 7. Reverse recovery definitions; ramp recovery

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11. Package outline



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12. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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